A Current-Mode DRAM for CVNS

Report of A Work In Progress

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June 13, 2008

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  - Introduction
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Motivation

- Memory Design
  - Compactness
  - More than 1 bit storage on each cell
  - Low refreshing rate
  - Fast read/write
- CVNS, a potential candidate

Introduction to CVNS

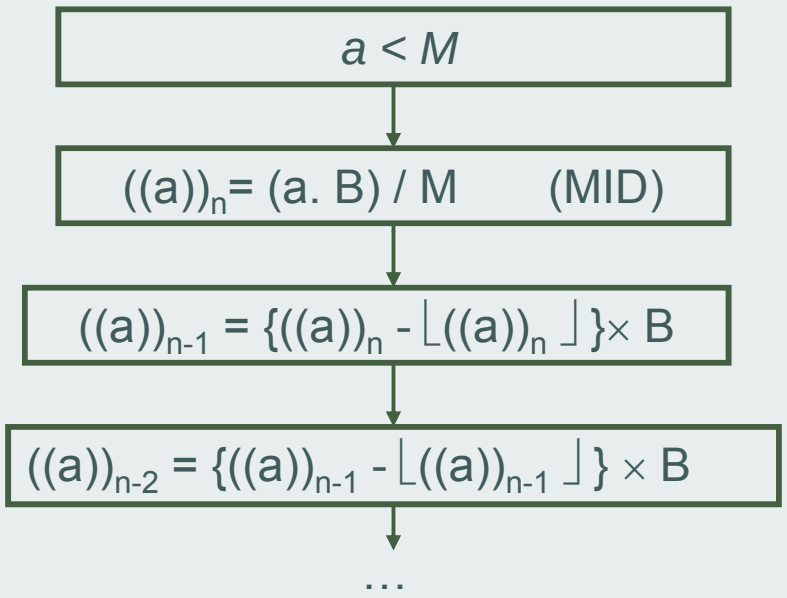
- Continuous Valued Number System
- Non-integer modular arithmetic with positive radix
- Uses classical analog circuits for implementation
- Analog arithmetic advantages
  - High Speed
  - Limited interconnections
  - Reduced Area
  - Reduced system and cross-talk noise
- Allows for arbitrary accuracy of arithmetic circuits

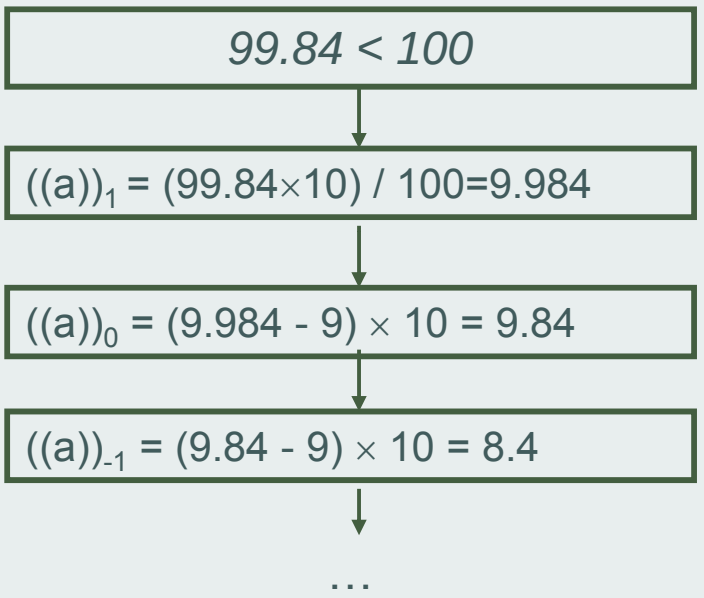
Digit Generation in CVNS

- Cascade Digit Generation

Calculates the radix- B CVNS digits in serial, starting from MID

- Modular Digit Generation

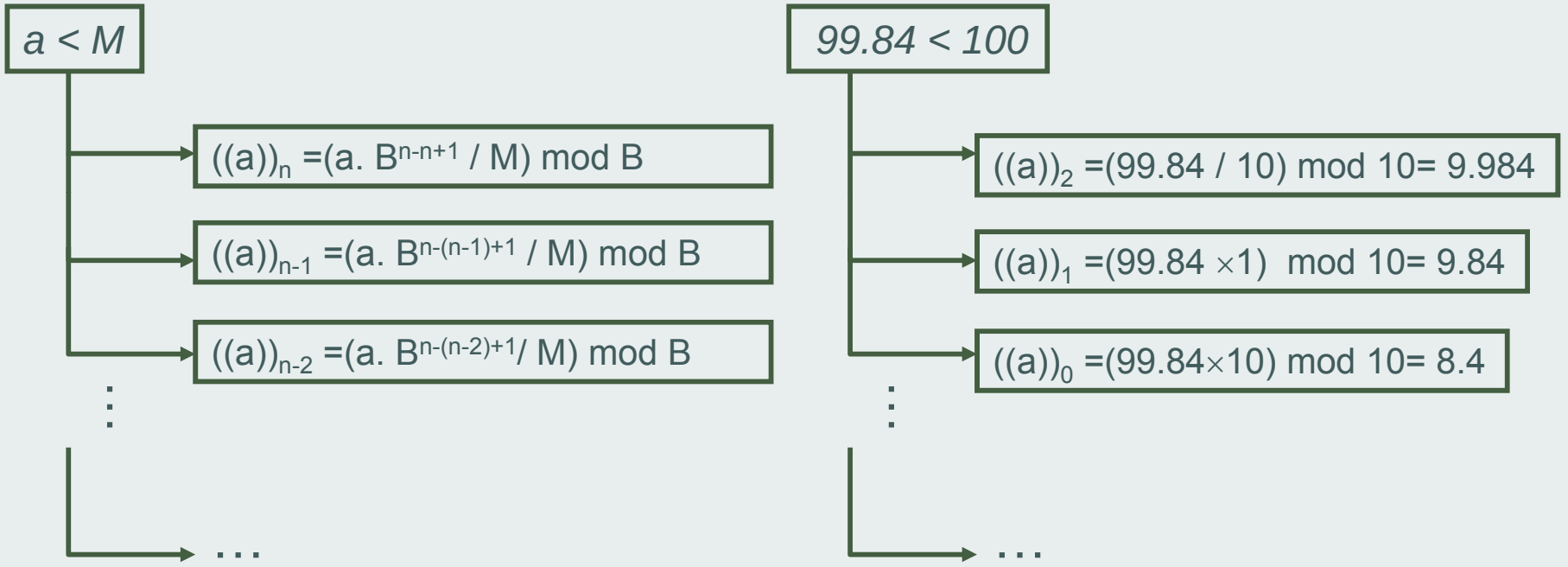




Digit Generation in CVNS

- Cascade Digit Generation
- Modular Digit Generation

Computes all of the radix- B CVNS digits in parallel, independent of each other



$(\alpha) \bmod \beta = \alpha - \beta \lfloor \alpha / \beta \rfloor$

Error Correction in CVNS

- Digit Recovering
  - Chain-like relationship between digits (overlap)
- Reverse Evolution (RE) Method
  - Increases the accuracy of analog digits
  - A sequential process

Error Correction in CVNS (Cont.)

- RE method

$((a))_i$ (original digit) $\quad k \le i \le n$

$\hookrightarrow$ $((a'))_i$ (errored digit) $= ((a))_i + \varepsilon_i$

$\hookrightarrow$ $[((a'))_i]_R = [((a'))_i - ((a''))_{i-1} / B]_R \bmod^{+} B \quad ((a')) \ge 0$

$[((a'))_i]_R = [((a'))_i - ((a''))_{i-1} / B]_R \bmod^{-} B \quad ((a')) < 0$

$\hookrightarrow$ $((a))''_i$ (corrected digit) $= \begin{cases} [((a'))_i]_R + ((a''))_{i-1} / B & i > K \\ ((a'))_i & i = K \end{cases}$

- $(a) \bmod^{+} B = (a \bmod B + B) \bmod B \quad 0 \le (a) \bmod^{+} B < B$
- $(a) \bmod^{-} B = (a \bmod B - B) \bmod B \quad -B < (a) \bmod^{-} B \le B$

Error Correction in CVNS (Cont.)

- Example for a random value; a = 9.9845, B= 10, error=±0.4

i	2	1	0	-1	-2
$((a))_i$	9.9845	9.845	8.45	4.5	5

Error is introduced to each digit

$((a'))_i$	10.3845	10.245	8.05	4.9	5.4

$[9.39996]_R = 9$ $[9.3996]_R = 9$ $[7.596]_R = 8$ $[4.36]_R = 4$

9.8454 / 10 8.454 / 10 4.54 / 10 5.4 / 10

9.98454	9.8454	8.454	4.54	5.4

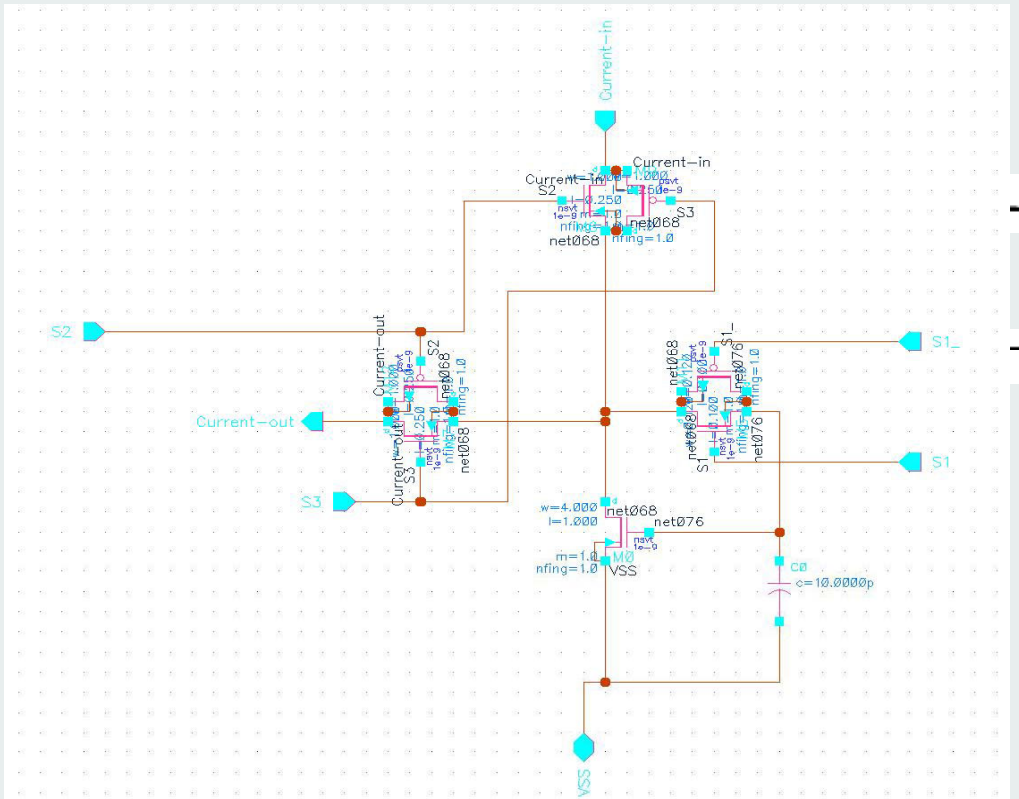
Error propagation from LID to MID $\varepsilon'_n = \varepsilon_k / B^{n-k}$

Introduction to Current-Mode DRAM

- Dynamic Random Access Memory
  - Memory cells requiring constant refreshing
    - Capacitor
    - Transistor
- Current-Mode DRAM
  - Fast sensing speed for the stored values
  - Capability of operating at lower power supply voltages

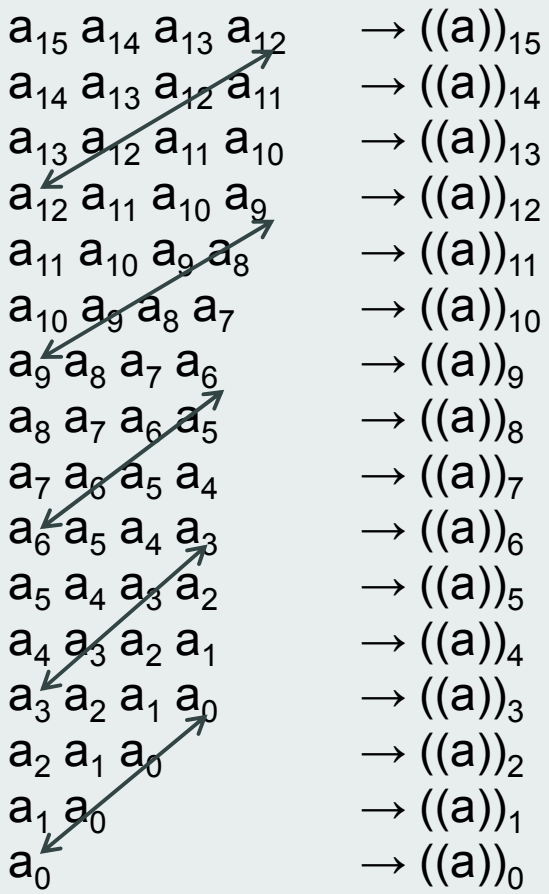
Storage Cell in Current-Mode DRAM

- Current Copier Cell as a Storage Element



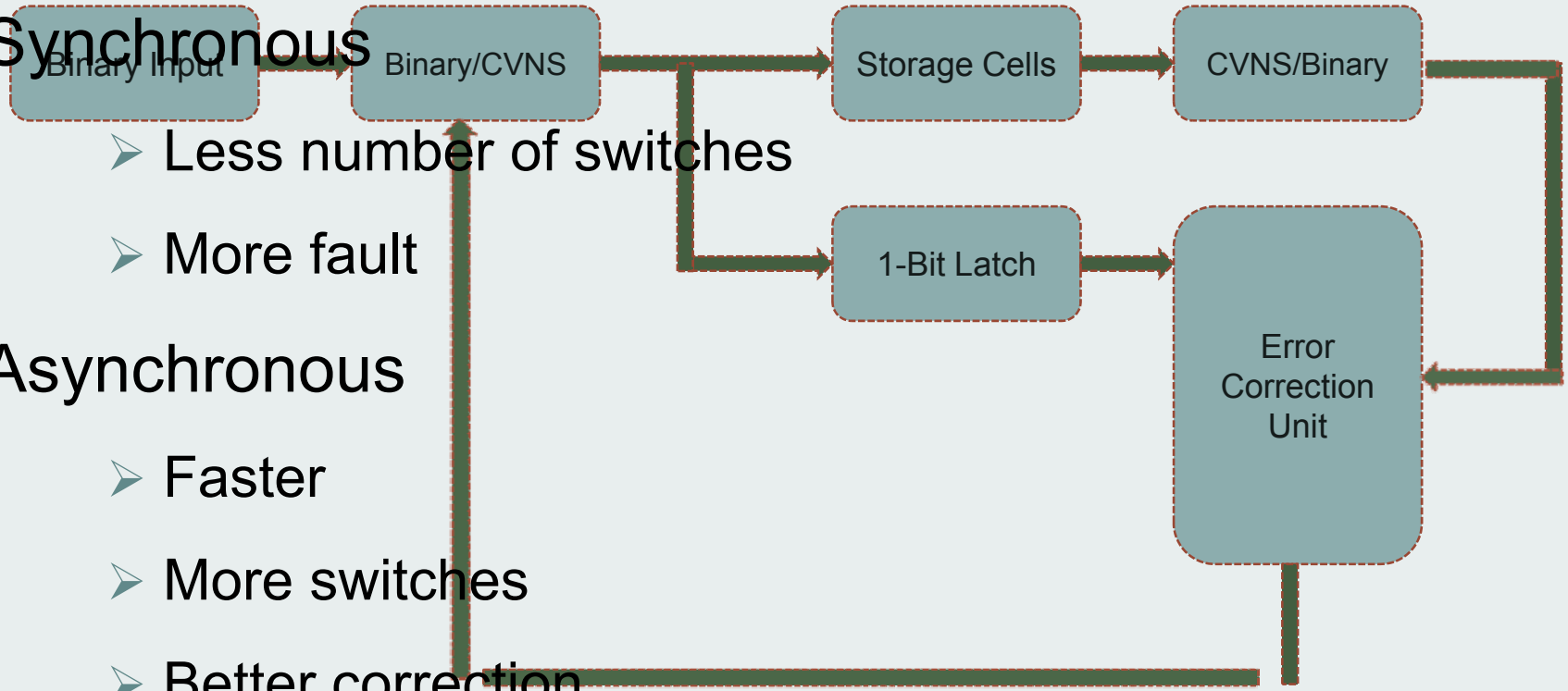
Current-Mode DRAM for CVNS

- Correction Using CVNS



Current-Mode DRAM for CVNS (Cont.)

- Block Diagram
- Synchronous
  - Less number of switches
  - More fault
- Asynchronous
  - Faster
  - More switches
  - Better correction

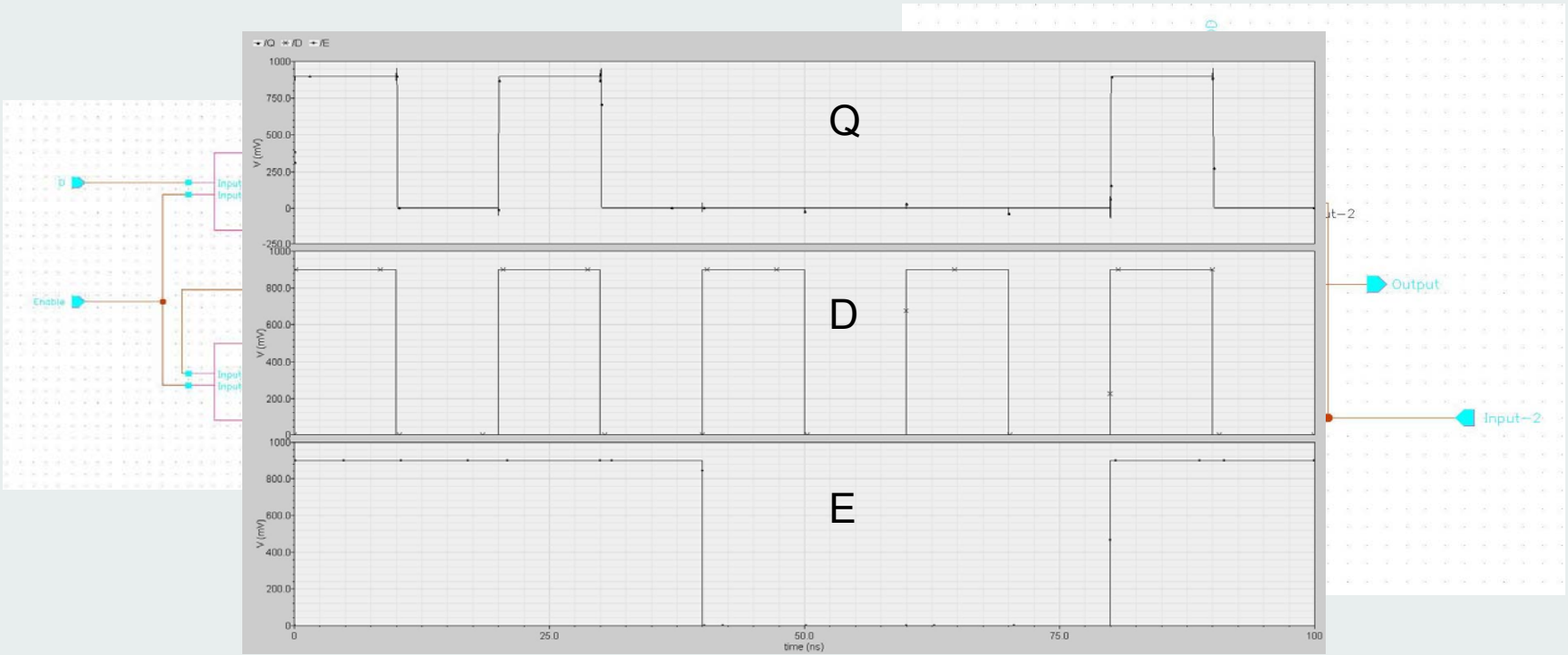


XOR

- Circuit
- Simula

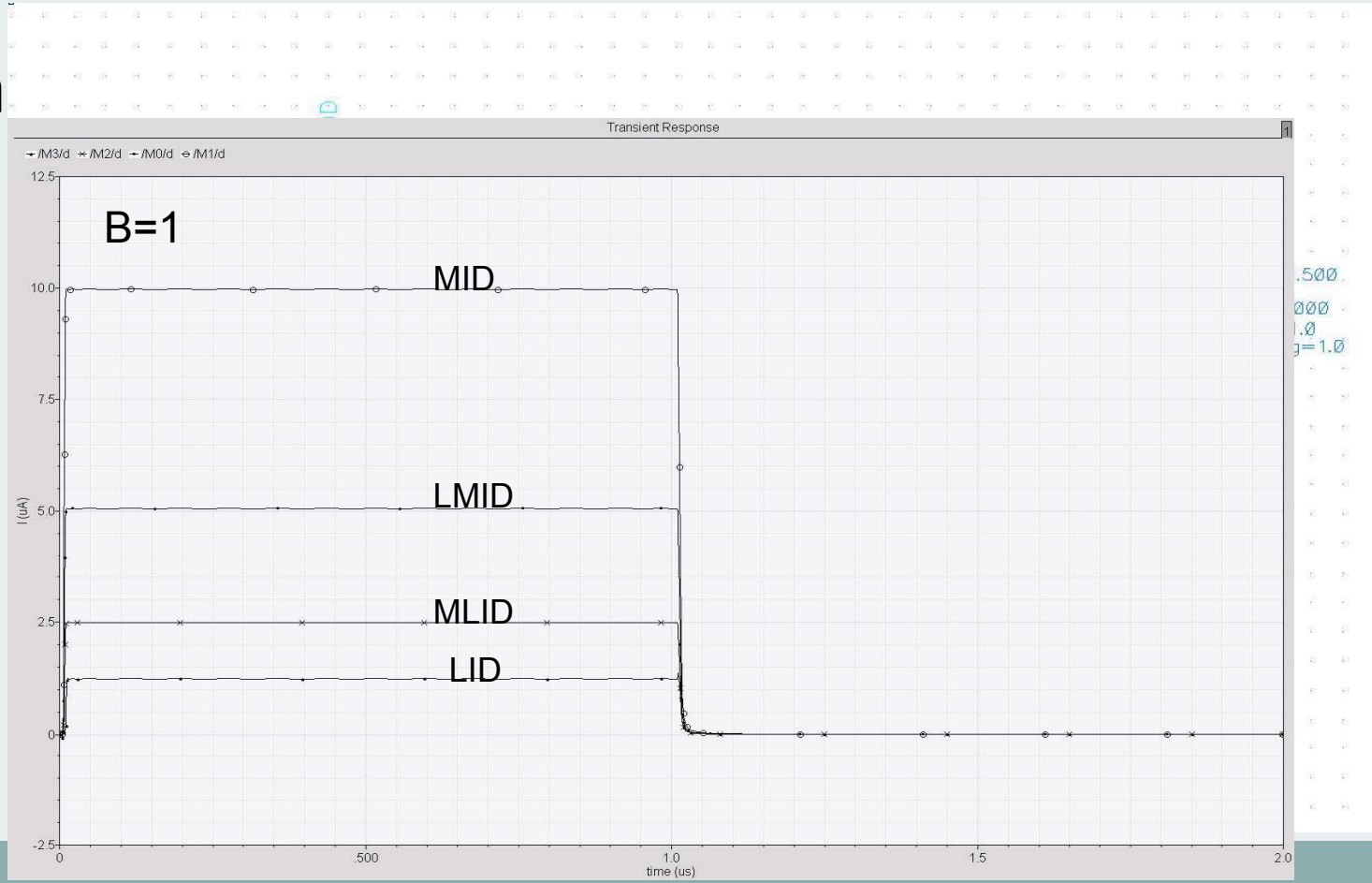
D-Latch

- Circuit
- Simulation Result



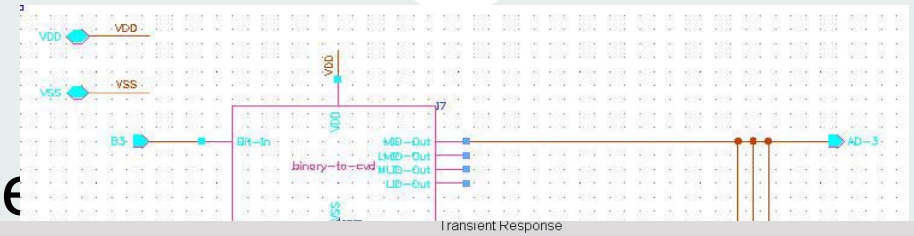
Binary To CVNS

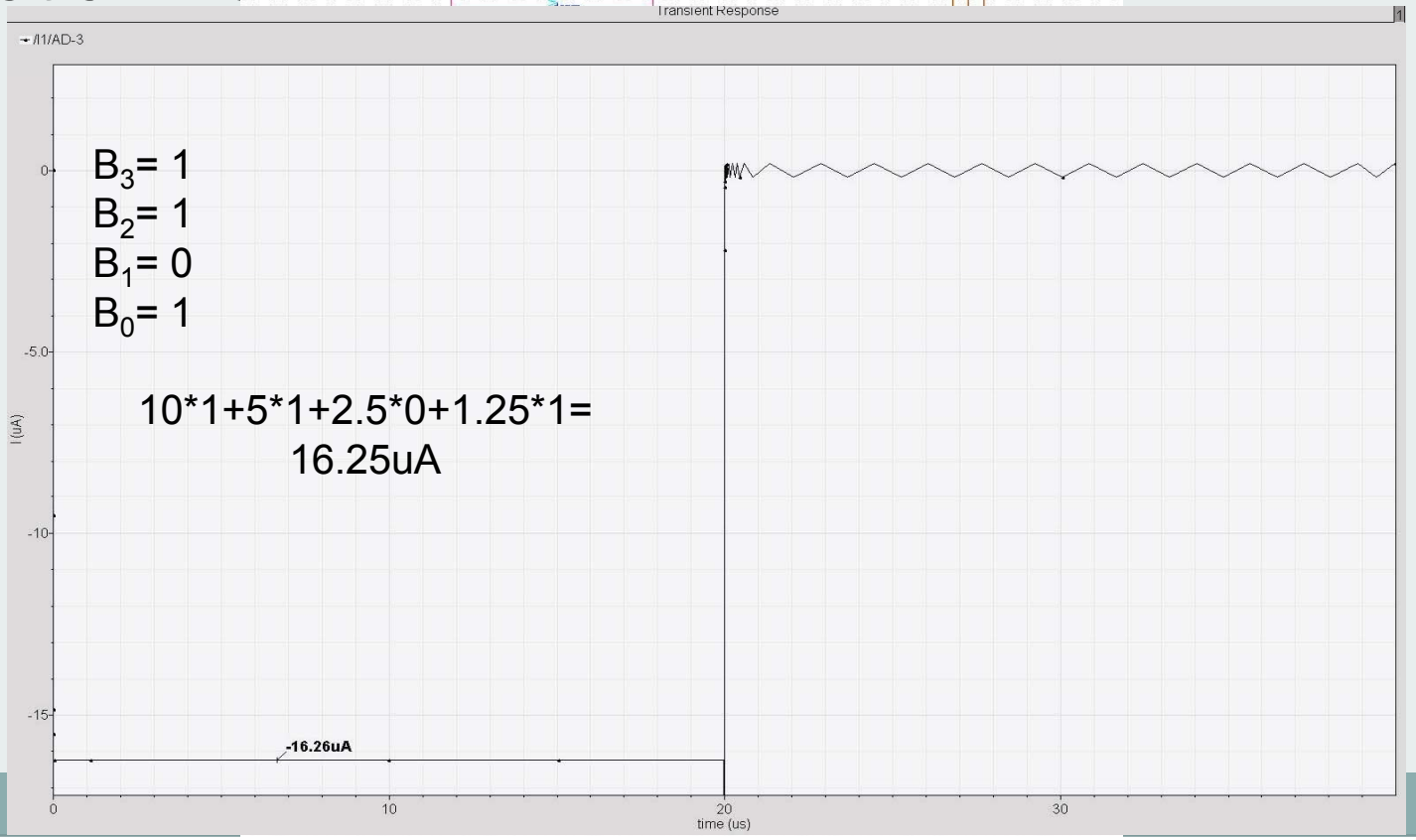
- Circuit
- Sim



Binary To CVNS (for 4-bit)

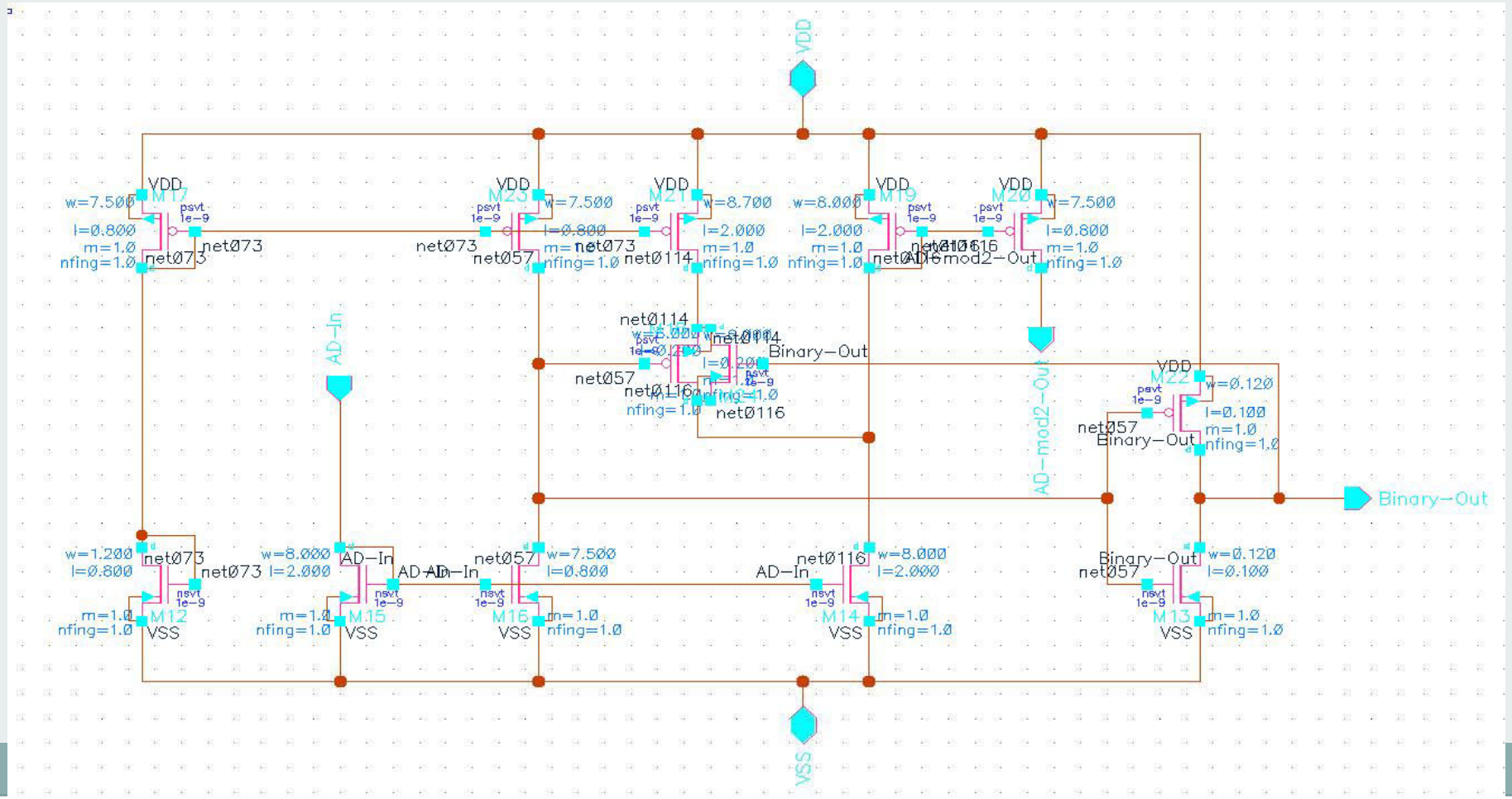
- Circuit
- Simulation Re





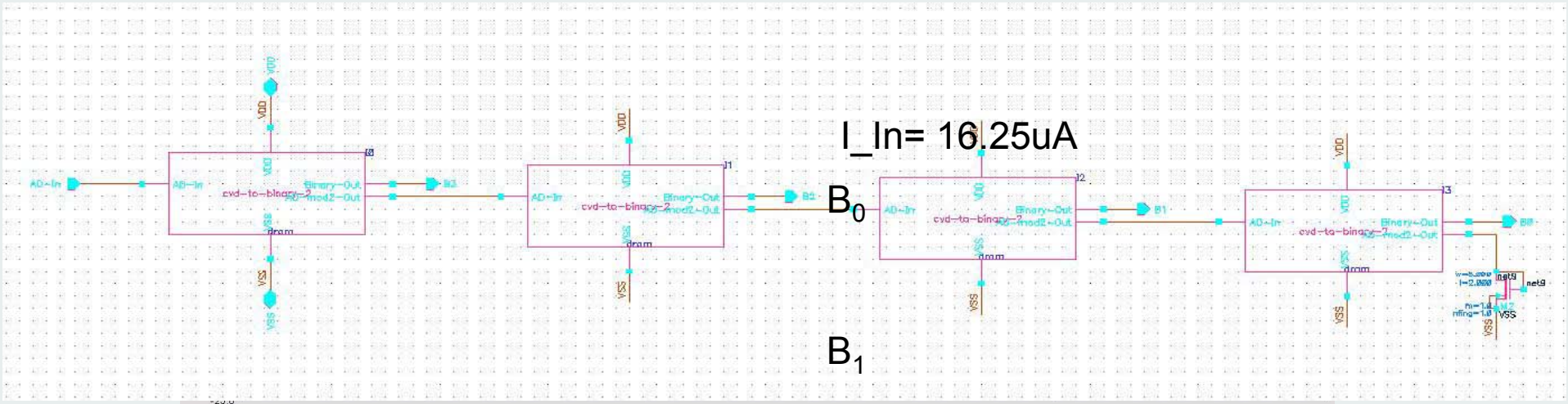
CVNS To Binary

- Circuit



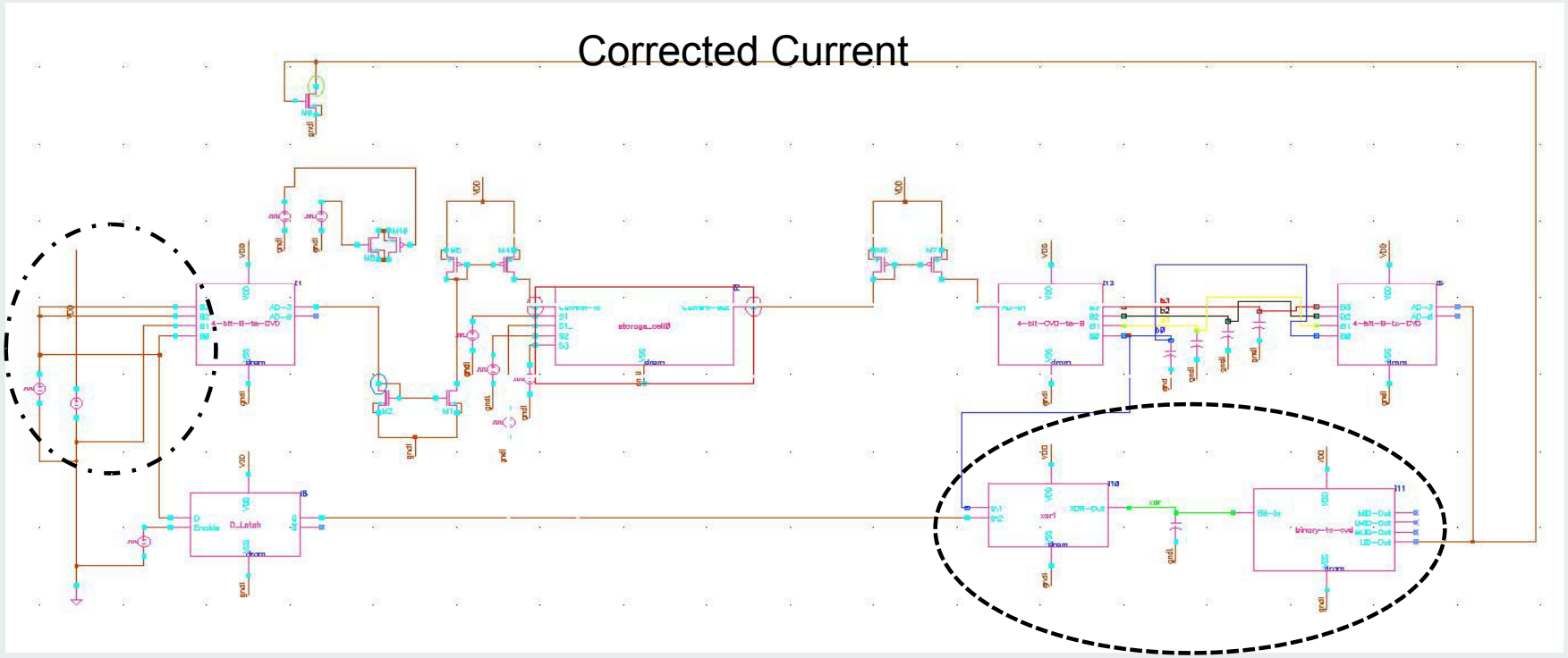
CVNS To Binary (for 4-bit)

- Circuit



Refresh Circuit

- Simulated Circuit



Refresh Circuit (Cont.)

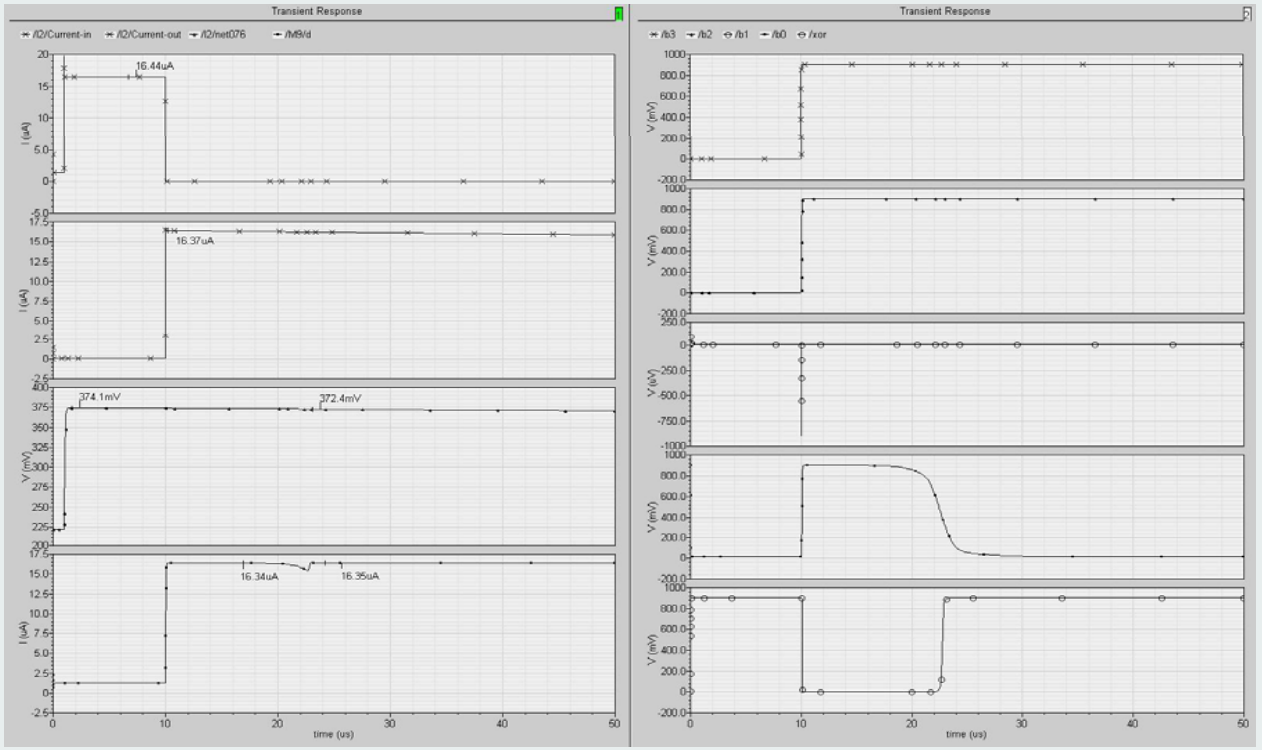
- Simulation Result

Current-In

Current-Out

V_C

Corrected-Current



B_3

B_2

B_1

B_0

XOR

Future Work

- Extend for 16-bit
- Draw the Layout